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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 1 of 2

Complete if Known	
Application Number	10/693,846
Filing Date	10/20/03
First Named Inventor	August et al.
Group Art Unit	Not Yet Assigned
Examiner Name	Not Yet Assigned
Attorney Docket Number	84,785

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	U.S. Patent Document Number	Kind Code[2] (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		6,075,261		Hossain et al.	06/13/2000	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Foreign Patent Document Office[3]	Number[4]	Kind Code[5] (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]

Examiner Signature		Date Considered	

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 2 of 2

Complete if Known	
Application Number	10/693,846
Filing Date	10/20/03
First Named Invent r	August et al.
Group Art Unit	Not Yet Assigned
Examiner Name	Not Yet Assigned
Attorney Docket Number	84,785

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
		MCGREGOR et al, "Self-Biased Boron-10 Coated High-Purity Epitaxial GaAs Thermal Neutron Detector" IEEE transactions on nuclear science, vol. 47, no., August 2000	
		MCGREGOR et al, " Recent Results From Thin-Film-Coated Semiconductor Neutron Detectors" X-Ray and Gamma-Ray Detector and Application IV, vol. 4784 (2002)	
		HAQUE et al, "Neutron dosimetry employing soft errors in dynamic random access memories" Phys. Med. Biol., 1989 vol. 34, no 9, 1195-1202 Printed in the UK	
		PHILLIPS et al, "Feasibility of a Neutron Detector-Dosemeter Based on Single-Event Upsets in Dynamic Random-Access Memories" Radiation Protection Dosimetry vol. 101, nos. 1-4, pp. 129-132 (2002) Nuclear Technology Publishing	
		ROBERTSON et al, "A class of boron-rich solid-state neutron detectors" Applied Physics Letters volume 80, number 19, 13 May 2002	
		GUARINI et at, "Electrical Integrity of State-of-the-Art 0.13 um SOI CMOS Devices and Circuits Transferred for Three-Dimensional (3D) Integrated Circuit (IC) Fabrication" 0-7803-7462-2/02 2002 IEEE	
		ARITA el al, "Experimental Investigation of Thermal Neutron-Induced Single Event Upset in Static Random Access Memories" Jpn. J. Appl. Phys Vol. 40 (2001) pp. L151-L153 Part 2, No. 2B, 15 February 2001	
		HUGHES et al, "Radiation Effects and Hardening of Mos Technology: Devices and Circuits" Preprint IEEE Trans. Nucl. Sci. June 2003	
		LUND et al. "Neutron Dosimeter Using a Dynamic Random Access Memory as a Sensor" IEEE *Transactions on Nuclear Science, Vol. 33. No. 1, February 1996*	
		PETERSEN et al. "Calculation of Cosmic-Ray Induced Soft Upsets and Scaling in VLSI Devices*" IEEE Transaction on Nuclear Science, Vol. NS-29, No. 6, December 1982	
		DAVIS "Use of Computer Memory Chips as The Basis For a Digital Albedo Neutron Dosimeter*" Health Physics Vol. 49, No. 2 (August), pp. 259-265, 1985 Printed in the U.S.A.	

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